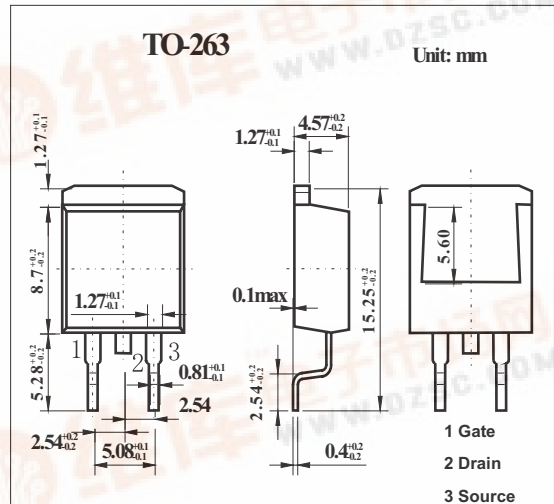


SMD Type Transistors

Silicon N-channel Power MOSFET  
2SK3637

■ Features

- Low on-resistance, low Qg
- High avalanche resistance



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Drain-source surrender voltage	V <sub>DSS</sub>	200	V
Gate-source surrender voltage	V <sub>GSS</sub>	±30	V
Drain current	I <sub>D</sub>	50	A
Peak drain current	I <sub>DP</sub>	200	A
Avalanche energy capability	E <sub>AS</sub>	2 000	mJ
Power dissipation Ta = 25°C	P <sub>D</sub>	3	W
Power dissipation		100	
Channel temperature	T <sub>ch</sub>	150	°C
Storage temperature	T <sub>stg</sub>	-55 to +150	°C

## 2SK3637

## ■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Gate-drain surrender voltage	V <sub>DSS</sub>	I <sub>D</sub> = 1 mA, V <sub>GS</sub> = 0	200			V
Diode forward voltage	V <sub>DSF</sub>	I <sub>DR</sub> = 50 A, V <sub>GS</sub> = 0			-1.5	V
Gate threshold voltage	V <sub>th</sub>	V <sub>DS</sub> = 25 V, I <sub>D</sub> = 10 mA	2		4	V
Drain-source cutoff current	I <sub>DSS</sub>	V <sub>DS</sub> = 160 V, V <sub>GS</sub> = 0			100	μA
Gate-source cutoff current	I <sub>GSS</sub>	V <sub>GS</sub> = ±30 V, V <sub>DS</sub> = 0			±1	μA
Drain-source on resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 25 A		29	40	mΩ
Forward transfer admittance	Y <sub>fs</sub>	V <sub>DS</sub> = 25 V, I <sub>D</sub> = 25 A	15	30		S
Short-circuit forward transfer capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0, f = 1 MHz		4 550		pF
Short-circuit output capacitance	C <sub>oss</sub>			750		pF
Reverse transfer capacitance	C <sub>rss</sub>			75		pF
Turn-on delay time	t <sub>d(on)</sub>	V <sub>DD</sub> = 100 V, I <sub>D</sub> = 25 A, R <sub>L</sub> = 4 Ω, V <sub>GS</sub> = 10 V		50		ns
Rise time	t <sub>r</sub>			125		ns
Turn-off delay time	t <sub>d(off)</sub>			390		ns
Fall time	t <sub>f</sub>			140		ns
Reverse recovery time	t <sub>rr</sub>	L = 230 μH, V <sub>DD</sub> = 100 V		210		ns
Reverse recovery charge	Q <sub>rr</sub>	I <sub>DR</sub> = 25 A, di/dt = 100 A/μs		820		nC
Total gate charge	Q <sub>g</sub>	V <sub>DD</sub> = 100 V, I <sub>D</sub> = 25 A, V <sub>GS</sub> = 10 V		85		nC
Gate-source charge	Q <sub>gs</sub>			30		nC
Gate-drain charge	Q <sub>gd</sub>			12		nC
Channel-case heat resistance	R <sub>th(ch-c)</sub>				1.25	°C/W
Channel-atmosphere heat resistance	R <sub>th(ch-a)</sub>				41.6	°C/W